# 2N3771, 2N3772

2N3771 is a Preferred Device

# High Power NPN Silicon Power Transistors

These devices are designed for linear amplifiers, series pass regulators, and inductive switching applications.

### Features

- Forward Biased Second Breakdown Current Capability  $I_{S/b} = 3.75$  Adc @  $V_{CE} = 40$  Vdc - 2N3771= 2.5 Adc @  $V_{CE} = 60$  Vdc - 2N3772
- Pb–Free Packages are Available\*

#### MAXIMUM RATINGS (Note 1)

Rating	Symbol	2N3771	2N3772	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	40	60	Vdc
Collector-Emitter Voltage	V <sub>CEX</sub>	50	80	Vdc
Collector-Base Voltage	V <sub>CB</sub>	50	100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	7.0	Vdc
Collector Current – Continuous Peak	Ι <sub>C</sub>	30 30	20 30	Adc
Base Current – Continuous Peak	Ι <sub>Β</sub>	7.5 15	5.0 15	Adc
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above 25°C			W W/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Case	θJC	1.17	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC registered data.



## **ON Semiconductor®**

http://onsemi.com

## 20 and 30 AMPERE POWER TRANSISTORS NPN SILICON 40 and 60 VOLTS, 150 WATTS



### ORDERING INFORMATION

Device	Package	Shipping
2N3771	TO-204	100 Units / Tray
2N3771G	TO–204 (Pb–Free)	100 Units / Tray
2N3772	TO-204	100 Units / Tray
2N3772G	TO–204 (Pb–Free)	100 Units / Tray

Preferred devices are recommended choices for future use and best overall value.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N3771, 2N3772

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2 and 3) $(I_C = 0.2 \text{ Adc}, I_B = 0)$	2N3771 2N3772	V <sub>CEO(sus)</sub>	40 60		Vdc
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 0.2 Adc, V <sub>EB(off)</sub> = 1.5 Vdc, R <sub>BE</sub> = 100 $\Omega$ )	2N3771 2N3772	V <sub>CEX(sus)</sub>	50 80		Vdc
Collector–Emitter Sustaining Voltage $(I_C = 0.2 \text{ Adc}, R_{BE} = 100 \Omega)$	2N3771 2N3772	V <sub>CER(sus)</sub>	45 70		Vdc
Collector Cutoff Current (Note 2) $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 50 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 25 \text{ Vdc}, I_B = 0)$	2N3771 2N3772	ICEO		10 10	mAdc
	2N3771 2N3772 2N6257 2N3771 2N3772	I <sub>CEV</sub>	- - - -	2.0 5.0 4.0 10 10	mAdc
Collector Cutoff Current (Note 2) $(V_{CB} = 50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$	2N3771 2N3772	I <sub>СВО</sub>		2.0 5.0	mAdc
Emitter Cutoff Current (Note 2) $(V_{BE} = 5.0 \text{ Vdc}, I_C = 0)$ $(V_{BE} = 7.0 \text{ Vdc}, I_C = 0)$	2N3771 2N3772	I <sub>EBO</sub>	_ _	5.0 5.0	mAdc
ON CHARACTERISTICS (Note 2)		1		1	
DC Current Gain (Note 3) $(I_C = 15 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$ $(I_C = 10 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$ $(I_C = 8.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$	2N3771 2N3772	h <sub>FE</sub>	15 15	60 60	-
$(I_{C} = 30 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$ $(I_{C} = 20 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$	2N3771 2N3772		5.0 5.0		
Collector-Emitter Saturation Voltage ( $I_C = 15 \text{ Adc}, I_B = 1.5 \text{ Adc}$ ) ( $I_C = 10 \text{ Adc}, I_B = 1.0 \text{ Adc}$ ) ( $I_C = 30 \text{ Adc}, I_B = 6.0 \text{ Adc}$ ) ( $I_C = 20 \text{ Adc}, I_B = 4.0 \text{ Adc}$ )	2N3771 2N3772 2N3771 2N3772	V <sub>CE(sat)</sub>	- - - -	2.0 1.4 4.0 4.0	Vdc
$\begin{array}{l} \text{Base-Emitter On Voltage} \\ (I_{C} = 15 \; \text{Adc}, \; V_{CE} = 4.0 \; \text{Vdc}) \\ (I_{C} = 10 \; \text{Adc}, \; V_{CE} = 4.0 \; \text{Vdc}) \\ (I_{C} = 8.0 \; \text{Adc}, \; V_{CE} = 4.0 \; \text{Vdc}) \end{array}$	2N3771 2N3772	V <sub>BE(on)</sub>	- -	2.7 2.2	Vdc
*DYNAMIC CHARACTERISTICS (Note 2)					
Current–Gain — Bandwidth Product ( $I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f_{test} = 50 \text{ kHz}$ )		f <sub>T</sub>	0.2	-	MHz
Small–Signal Current Gain $(I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f = 1.0 \text{ kHz})$		h <sub>fe</sub>	40	-	-
SECOND BREAKDOWN		•	•		
Second Breakdown Energy with Base Forward Biased, t = 1.0 s (non-repet $(V_{CE} = 40 \text{ Vdc})$ $(V_{CE} = 60 \text{ Vdc})$	itive) 2N3771 2N3772	I <sub>S/b</sub>	3.75 2.5		Adc

Indicates JEDEC registered data.
Pulse Test: 300 μs, Rep. Rate 60 cps.





Figure 2. Thermal Response — 2N3771, 2N3772



Figure 3. Active–Region Safe Operating Area — 2N3771, 2N3772

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation: i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

Figure 3 is based on JEDEC registered Data. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 200^{\circ}$ C.  $T_{J(pk)}$  may be calculated from the data of Figure 2. Using data of Figure 2 and the pulse power limits of Figure 3,  $T_{J(pk)}$  will be found to be less than  $T_{J(max)}$  for pulse widths of 1 ms and less. When using ON Semiconductor transistors, it is permissible to increase the pulse power limits until limited by  $T_{J(max)}$ .



D1 MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE I\_B  $\approx$  100 mA MSD6100 USED BELOW I\_B  $\approx$  100 mA

Figure 4. Switching Time Test Circuit



Figure 5. Turn-On Time



#### PACKAGE DIMENSIONS

TO-204 (TO-3) CASE 1-07 ISSUE Z





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI

Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

			-	
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37 REF	
В		1.050		26.67
С	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
Е	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
Н	0.215	0.215 BSC		BSC
K	0.440	0.480	11.18	12.19
L	0.665	BSC	16.89	BSC
N		0.830		21.08
Q	0.151	0.165	3.84	4.19
U	1.187	BSC	30.15 BSC	
۷	0.131	0.188	3.33	4.77

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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